

# Kl Pey

## List of Publications by Year in descending order

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papers

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citations

1162889

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docs citations

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times ranked

298  
citing authors

#	ARTICLE	IF	CITATIONS
1	Effect of Copper TSV Annealing on Via Protrusion for TSV Wafer Fabrication. Journal of Electronic Materials, 2012, 41, 2533-2542.	1.0	136
2	New salicidation technology with Ni(Pt) alloy for MOSFETs. IEEE Electron Device Letters, 2001, 22, 568-570.	2.2	85
3	Polarity-dependent dielectric breakdown-induced epitaxy (DBIE) in Si MOSFETs. IEEE Electron Device Letters, 2002, 23, 526-528.	2.2	62
4	Gate Dielectric-Breakdown-Induced Microstructural Damage in MOSFETs. IEEE Transactions on Device and Materials Reliability, 2004, 4, 38-45.	1.5	31
5	Evidence for Two Distinct Positive Trapped Charge Components in NBTI Stressed p-MOSFETs Employing Ultrathin CVD Silicon Nitride Gate Dielectric. IEEE Electron Device Letters, 2004, 25, 637-639.	2.2	26
6	Stress-induced voiding in multi-level copper/low-k interconnects. , 0, , .		11
7	New insight into gate dielectric breakdown induced MOSFET degradation by novel percolation path resistance measurements. , 0, , .		11
8	Ni(Pt) alloy silicidation on (100) Si and poly-silicon lines. Thin Solid Films, 2004, 462-463, 137-145.	0.8	10
9	Improved electrical performance of erbium silicide Schottky diodes formed by Pre-RTA amorphization of Si. IEEE Electron Device Letters, 2006, 27, 93-95.	2.2	9
10	In situ XRD analysis of Ni(Pt)/Si(100) reactions in low temperature regime $\approx 400^{\circ}\text{C}$ . Solid State Communications, 2003, 128, 325-328.	0.9	8
11	Percolation resistance evolution during progressive breakdown in narrow MOSFETs. IEEE Electron Device Letters, 2006, 27, 396-398.	2.2	8
12	Stress migration reliability of wide CU interconnects with gouging vias. , 0, , .		7
13	Stress-induced voiding beneath vias with wide copper metal leads. , 0, , .		6
14	Multiple-pulse laser thermal annealing for the formation of Co-silicided junction. IEEE Electron Device Letters, 2006, 27, 237-239.	2.2	5
15	Characterization of the junction leakage of Ti-capped Ni-silicided junctions. Thin Solid Films, 2004, 462-463, 202-208.	0.8	4
16	Investigation of intrinsic dielectric breakdown mechanism in Cu/low- $\kappa$ /interconnect system. IEEE Electron Device Letters, 2006, 27, 234-236.	2.2	4
17	Novel dielectric slots in Cu interconnects for suppressing stress-induced void failure. , 0, , .		3
18	Study of dielectric-breakdown-induced dopant redistribution based on MOSFET diode I-V measurement. , 0, , .		3

#	ARTICLE	IF	CITATIONS
19	Exponential dependence of percolation resistance on gate voltage and its impacts on progressive breakdown. , 0, , .		3
20	Low-frequency noise measurement of copper damascene interconnects. , 0, , .		2
21	Dielectric-breakdown-induced epitaxy: a universal breakdown defect in ultrathin gate dielectrics. , 0, , .		1
22	Structural analysis of breakdown in ultrathin gate dielectrics using transmission electron microscopy. , 0, , .		1
23	Expanded Papers From the 2003 IEEE International Symposium on the Physical and Failure Analysis of Integrated Circuits (IPFA). IEEE Transactions on Device and Materials Reliability, 2004, 4, 4-4.	1.5	1
24	The effects of dielectric slots on Copper/Low-k interconnects reliability. , 2009, , .		1
25	Correction to "Polarity-dependent dielectric breakdown-induced epitaxy (DBIE) in Si MOSFETs". IEEE Electron Device Letters, 2002, 23, 676-676.	2.2	0
26	Introduction to the Special Issue on the 2004 IEEE International Symposium on the Physical and Failure Analysis of Integrated Circuits (IPFA). IEEE Transactions on Device and Materials Reliability, 2005, 5, 167-167.	1.5	0
27	Design for Manufacturability in Backend Reliability and Packaging of Nanoscale Technologies. , 2007, , .		0
28	Nature of breakdown in ultrathin gate dielectrics. , 2008, , .		0